



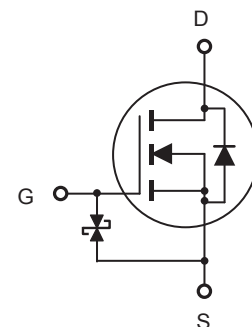
CED01N65/CEU01N65

N-Channel Enhancement Mode Field Effect Transistor

PRELIMINARY

FEATURES

- 650V, 1.2A, $R_{DS(ON)} = 10.5\Omega$ @ $V_{GS} = 10V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- Lead free product is acquired.
- TO-251 & TO-252 package.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	V
Drain Current-Continuous	I_D	1.2	A
Drain Current-Pulsed ^a	I_{DM}	4.8	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above 25°C	P_D	35.7	W
		0.29	W/ $^\circ\text{C}$
Operating and Store Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.5	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	$^\circ\text{C/W}$

This is preliminary information on a new product in development now .
Details are subject to change without notice .

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Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

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Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V$			25	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 30V, V_{DS} = 0V$			10	μA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -30V, V_{DS} = 0V$			-10	μA
On Characteristics ^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2.5		4.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.6A$		8.5	10.5	Ω
Dynamic Characteristics ^c						
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 0.6A$		1		S
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{ MHz}$		215		pF
Output Capacitance	C_{oss}			50		pF
Reverse Transfer Capacitance	C_{rss}			20		pF
Switching Characteristics ^c						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300V, I_D = 1.2A, V_{GS} = 10V, R_{GEN} = 4.7\Omega$		14.3	38.6	ns
Turn-On Rise Time	t_r			14.6	29.2	ns
Turn-Off Delay Time	$t_{d(off)}$			23	46	ns
Turn-Off Fall Time	t_f			17	34	ns
Total Gate Charge	Q_g	$V_{DS} = 480V, I_D = 1.2A, V_{GS} = 10V$		5.8	11.6	nC
Gate-Source Charge	Q_{gs}			1.9		nC
Gate-Drain Charge	Q_{gd}			2.4		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current	I_S				1.2	A
Drain-Source Diode Forward Voltage ^b	V_{SD}	$V_{GS} = 0V, I_S = 0.6A$			1.5	V
Notes : a.Repetitive Rating : Pulse width limited by maximum junction temperature. b.Device Mounted on FR4 Board, $t < 10\text{ sec.}$ c.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. d.Guaranteed by design, not subject to production testing.						

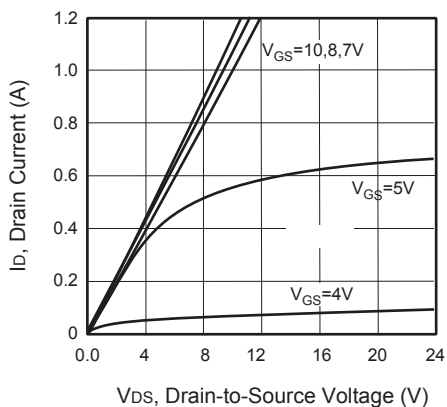


Figure 1. Output Characteristics

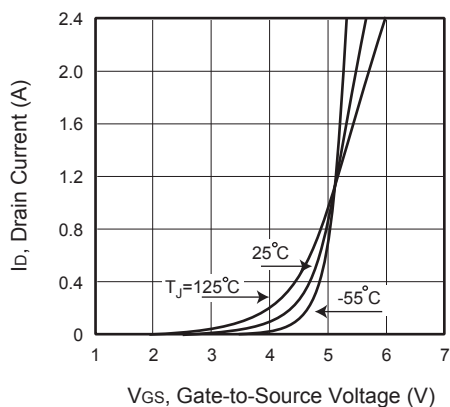


Figure 2. Transfer Characteristics

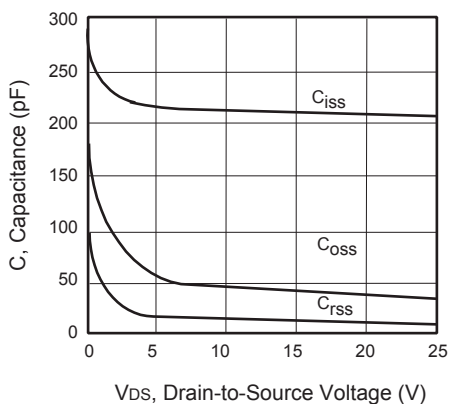


Figure 3. Capacitance

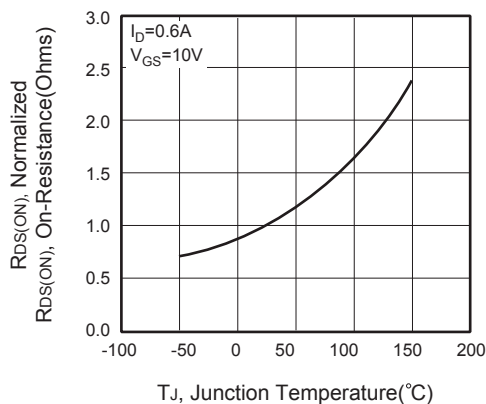


Figure 4. On-Resistance Variation with Temperature

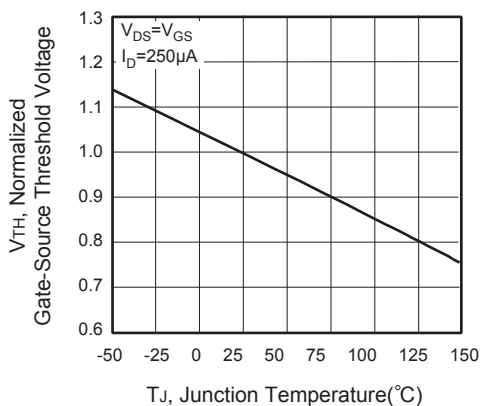


Figure 5. Gate Threshold Variation with Temperature

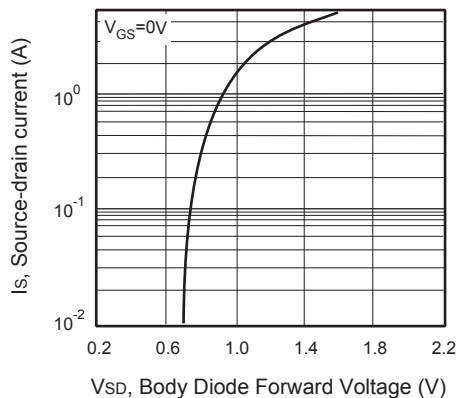


Figure 6. Body Diode Forward Voltage Variation with Source Current



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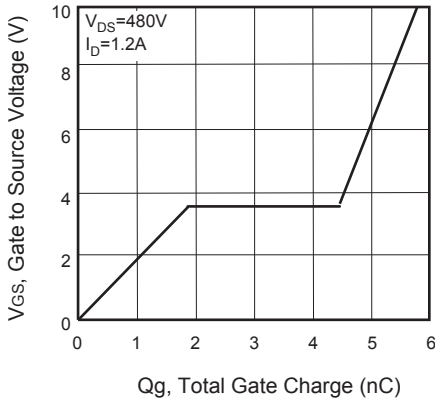


Figure 7. Gate Charge

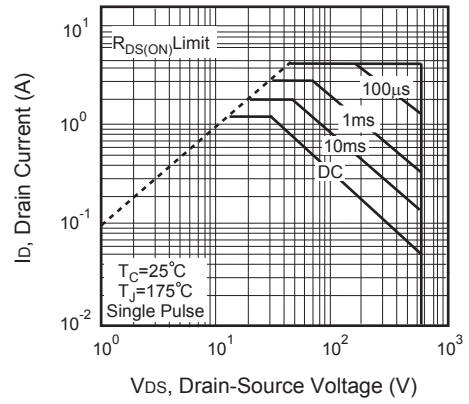


Figure 8. Maximum Safe Operating Area

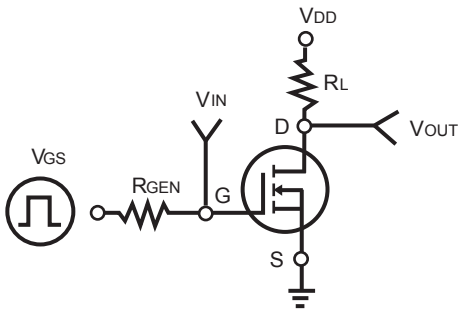


Figure 9. Switching Test Circuit

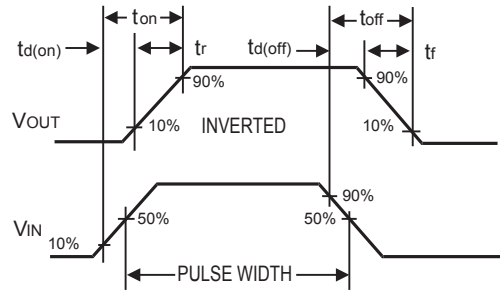


Figure 10. Switching Waveforms

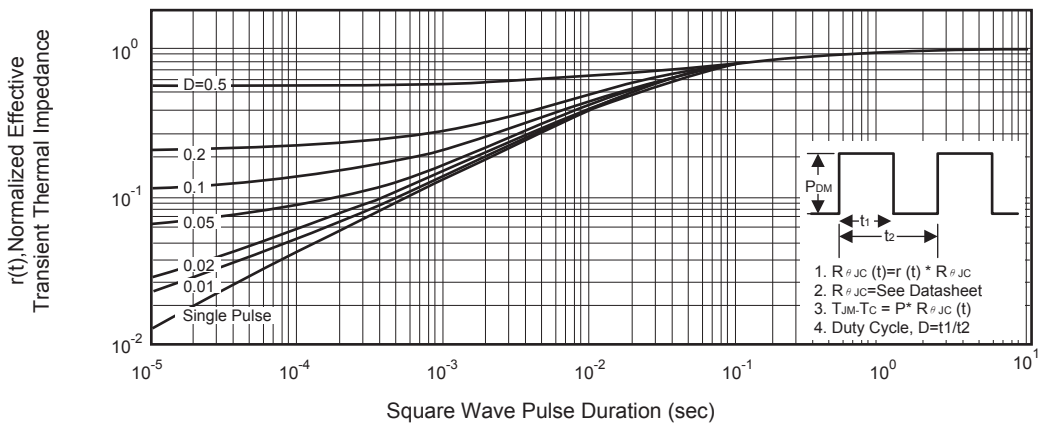


Figure 11. Normalized Thermal Transient Impedance Curve